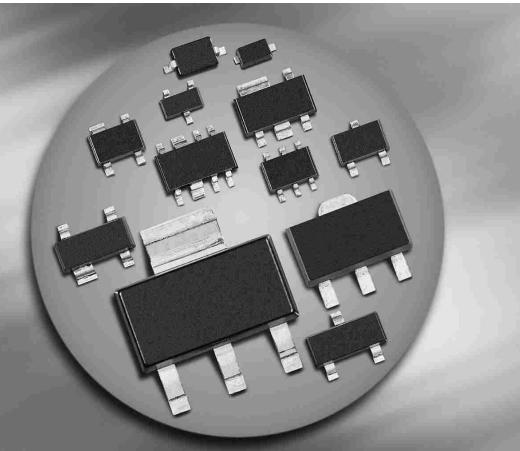
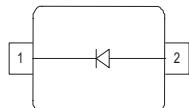


### Silicon PIN Diode

- Series diode for mobile communication in low loss transmit-receiver switches
- Band switch for TV-tuners
- Very low forward resistance (typ. 0.65 Ω @ 5 mA)
- Low capacitance (typ. 0.5 pF @ 0V)
- Fast switching applications
- Pb-free (RoHS compliant) package


**BAR65-02L**
**BAR65-02V**
**BAR65-03W**


Type	Package	Configuration	$L_S$ (nH)	Marking
BAR65-02L*	TSLP-2-1	single, leadless	0.4	NN
BAR65-02V	SC79	single	0.6	N
BAR65-03W	SOD323	single	1.8	blue M

\* Preliminary Data

**Maximum Ratings at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	30	V
Forward current	$I_F$	100	mA
Total power dissipation BAR65-02L, $T_S \leq 128^\circ\text{C}$ BAR65-02V, $T_S \leq 118^\circ\text{C}$ BAR65-03W, $T_S \leq 113^\circ\text{C}$	$P_{tot}$	250 250 250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating temperature range	$T_{op}$	-55 ... 125	
Storage temperature	$T_{stg}$	-55 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> BAR65-02L	$R_{thJS}$	$\leq 90$	K/W
BAR65-02V		$\leq 130$	
BAR65-03W		$\leq 145$	

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

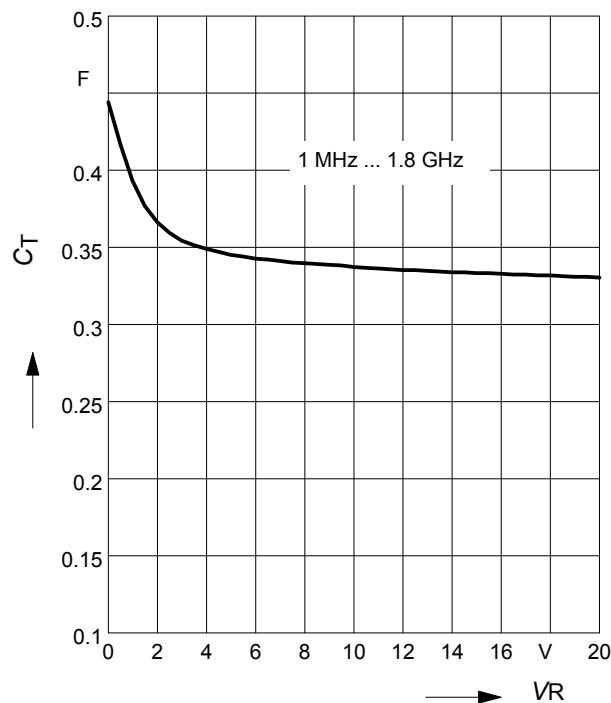
Reverse current $V_R = 20 \text{ V}$	$I_R$	-	-	20	nA
Forward voltage $I_F = 100 \text{ mA}$	$V_F$	-	0.93	1	V

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

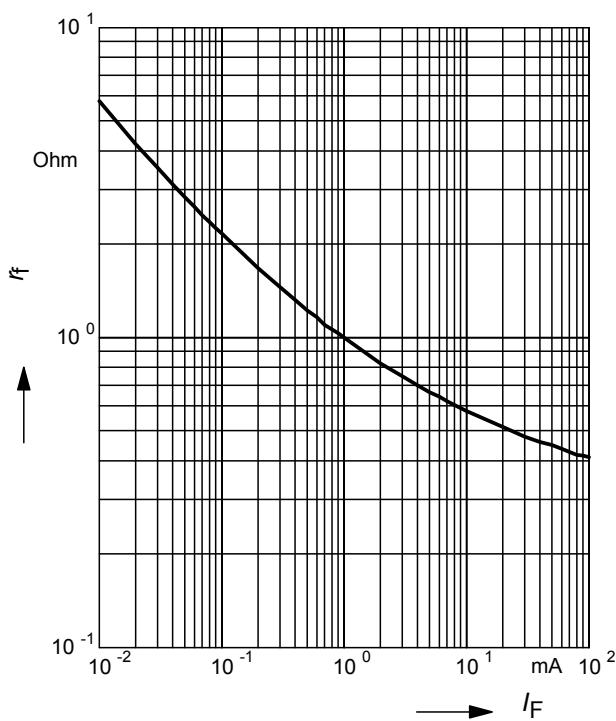
**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Diode capacitance $V_R = 1 \text{ V}, f = 1 \text{ MHz}$ $V_R = 3 \text{ V}, f = 1 \text{ MHz}$ $V_R = 0 \text{ V}, f = 100 \text{ MHz} \dots 1.8 \text{ GHz}$	$C_T$	-	0.45	0.9	pF
Reverse parallel resistance $V_R = 0 \text{ V}, f = 100 \text{ MHz}$ $V_R = 0 \text{ V}, f = 1 \text{ GHz}$ $V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$	$R_P$	-	700	-	kΩ
Forward resistance $I_F = 1 \text{ mA}, f = 100 \text{ MHz}$ $I_F = 5 \text{ mA}, f = 100 \text{ MHz}$ $I_F = 10 \text{ mA}, f = 100 \text{ MHz}$	$r_f$	-	1	-	Ω
Charge carrier life time $I_F = 10 \text{ mA}, I_R = 6 \text{ mA}, \text{measured at } I_R = 3 \text{ mA}, R_L = 100 \Omega$	$\tau_{rr}$	-	80	-	ns
I-region width	$W_I$	-	3.5	-	μm
Insertion loss <sup>1)</sup> $I_F = 1 \text{ mA}, f = 1.8 \text{ GHz}$ $I_F = 5 \text{ mA}, f = 1.8 \text{ GHz}$ $I_F = 10 \text{ mA}, f = 1.8 \text{ GHz}$	$I_L$	-	0.08	-	dB
Isolation <sup>1)</sup> $V_R = 0 \text{ V}, f = 0.9 \text{ GHz}$ $V_R = 0 \text{ V}, f = 1.8 \text{ GHz}$ $V_R = 0 \text{ V}, f = 2.45 \text{ GHz}$	$I_{SO}$	-	12	-	
<sup>1</sup> BAR65-02L in series configuration, $Z = 50\Omega$					

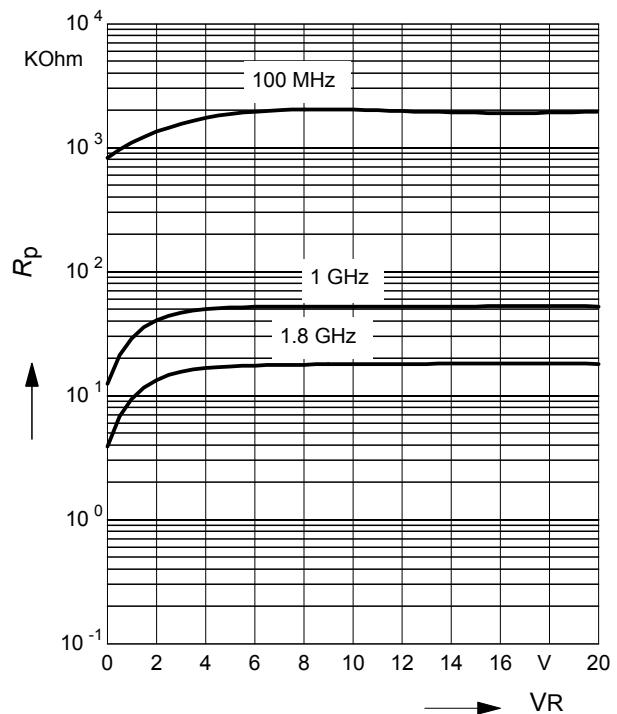
**Diode capacitance  $C_T = f(V_R)$**   
 $f$  = Parameter



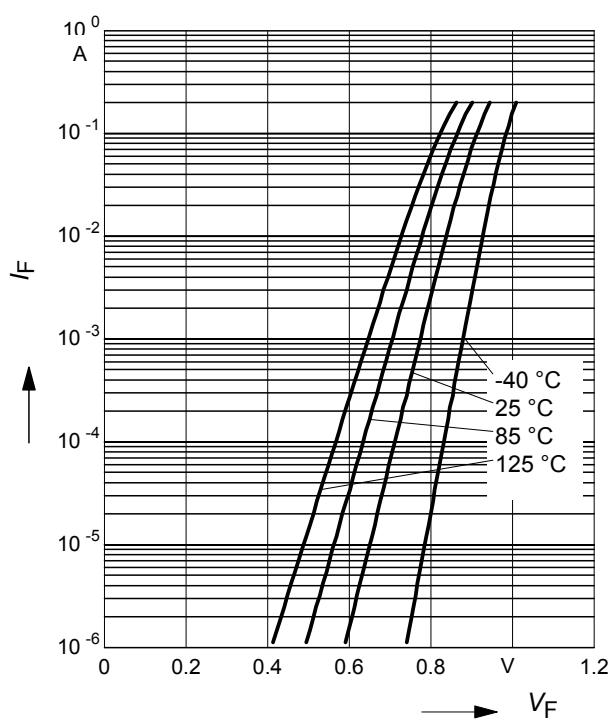
**Forward resistance  $r_f = f(I_F)$**   
 $f$  = 100MHz



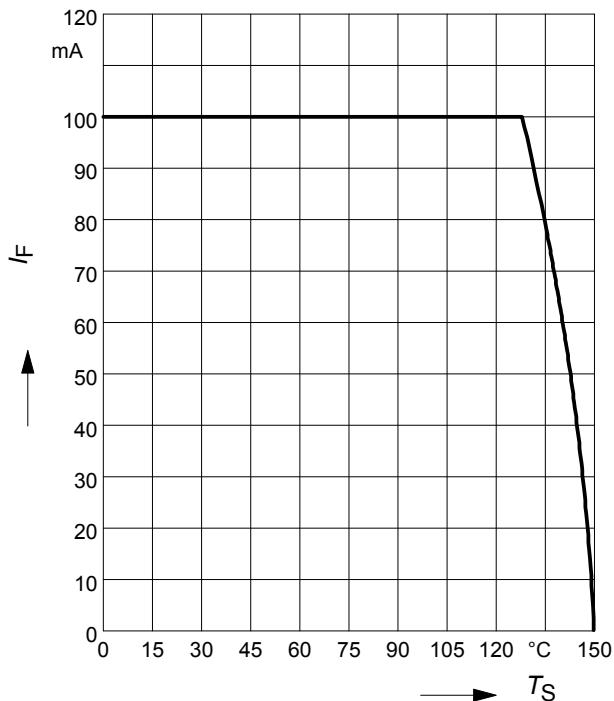
**Reverse parallel resistance  $R_P = f(V_R)$**   
 $f$  = Parameter



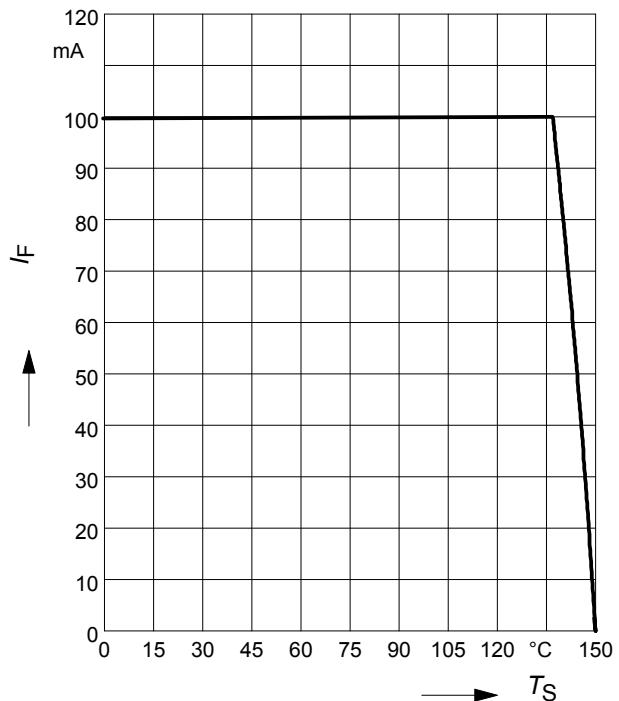
**Forward current  $I_F = f(V_F)$**   
 $T_A$  = Parameter



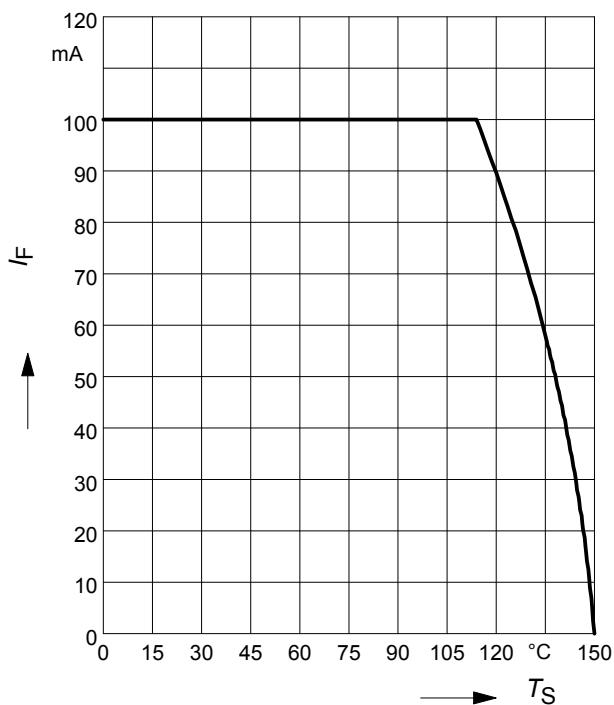
**Forward current  $I_F = f(T_S)$**   
BAR65-02L



**Forward current  $I_F = f(T_S)$**   
BAR65-02V

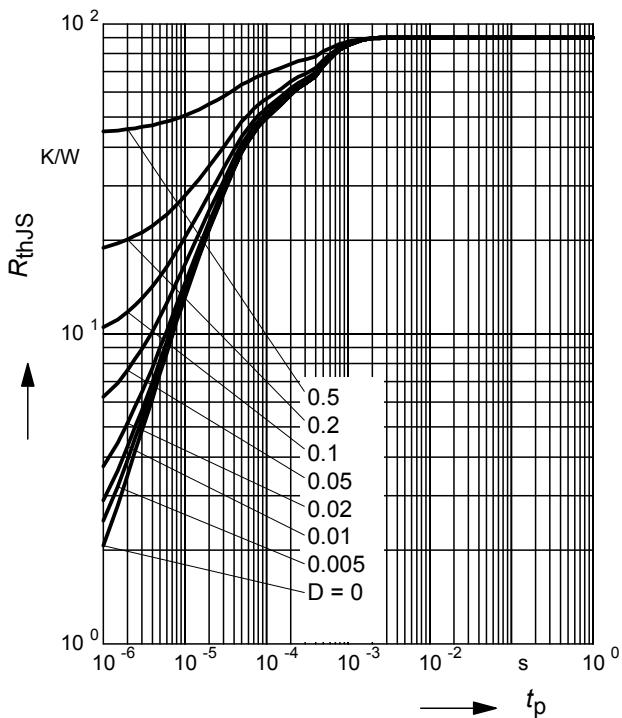


**Forward current  $I_F = f(T_S)$**   
BAR65-03W



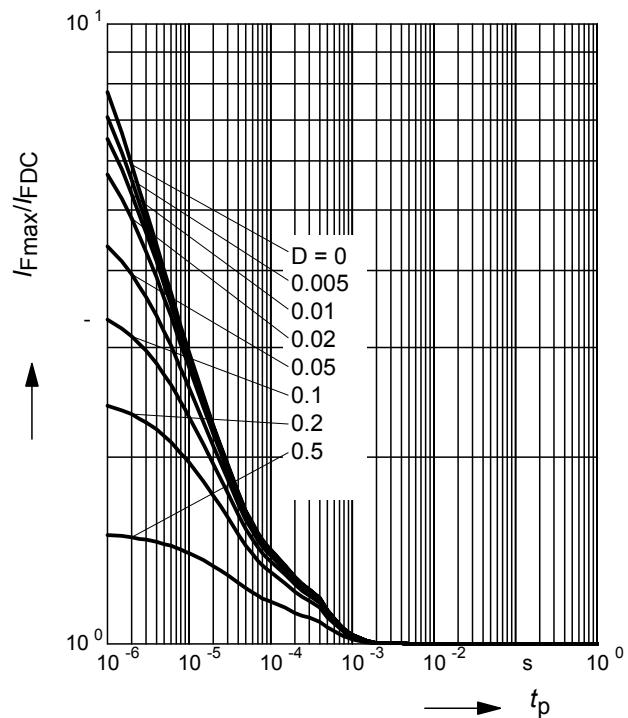
**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$** 

BAR65-02L

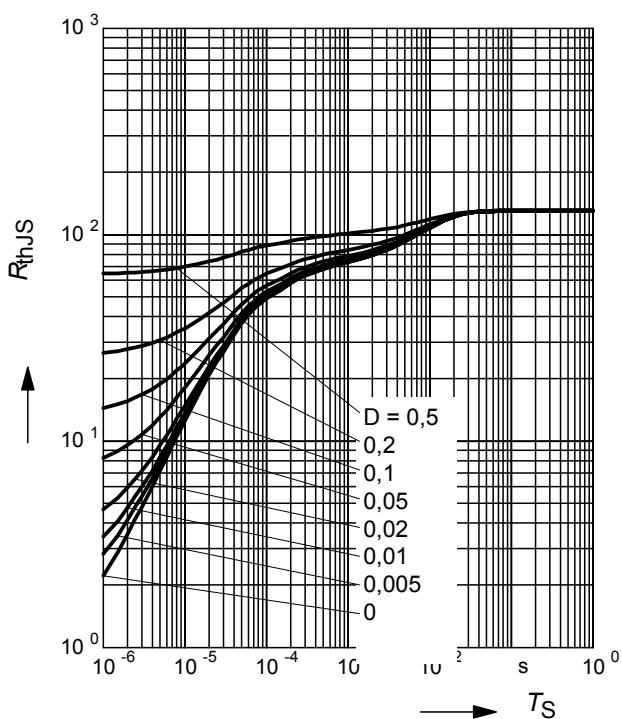

**Permissible Pulse Load**

$$I_{\text{Fmax}} / I_{\text{FDC}} = f(t_p)$$

BAR65-02L

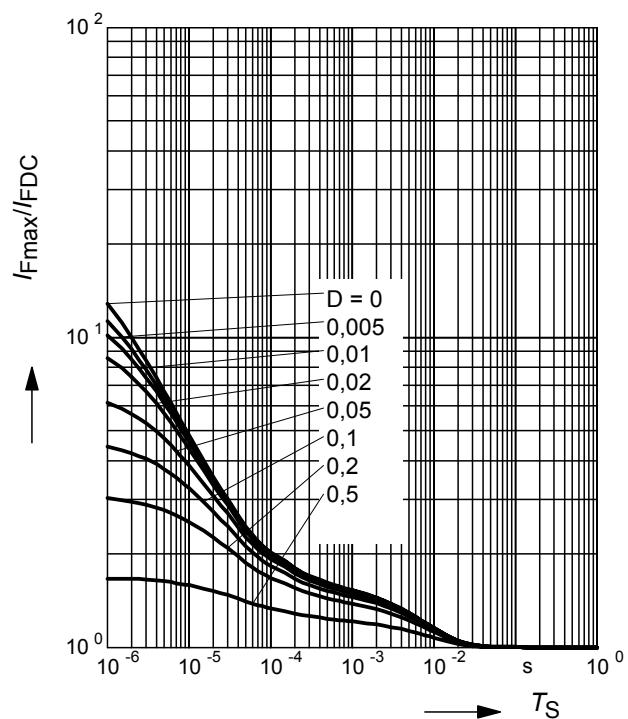

**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$** 

BAR65-02V


**Permissible Pulse Load**

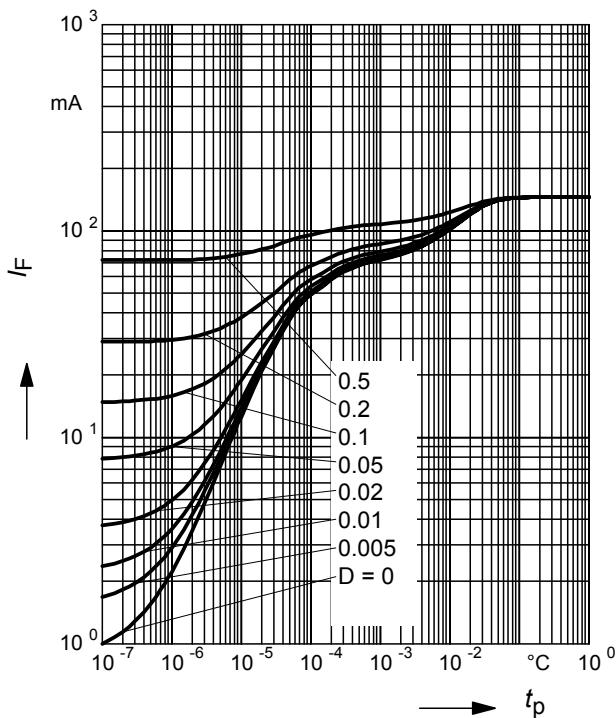
$$I_{\text{Fmax}} / I_{\text{FDC}} = f(T_S)$$

BAR65-02V



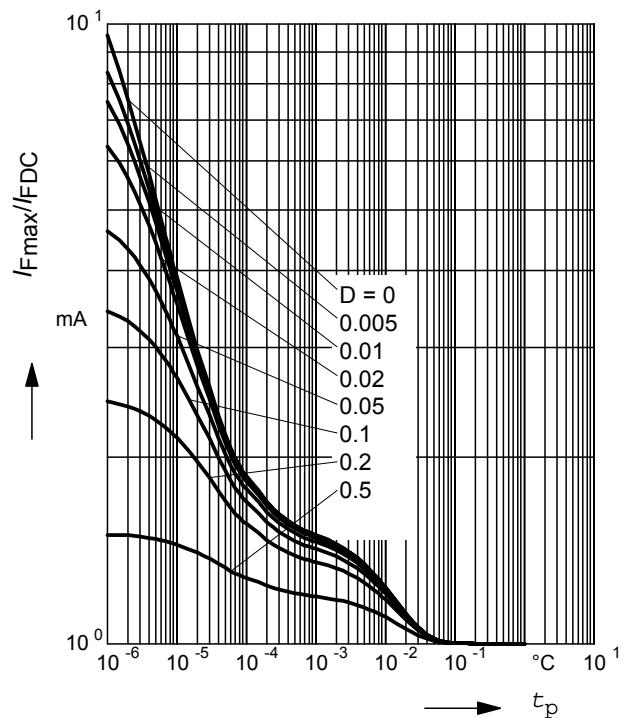
**Permissible Puls Load  $R_{thJS} = f(t_p)$** 

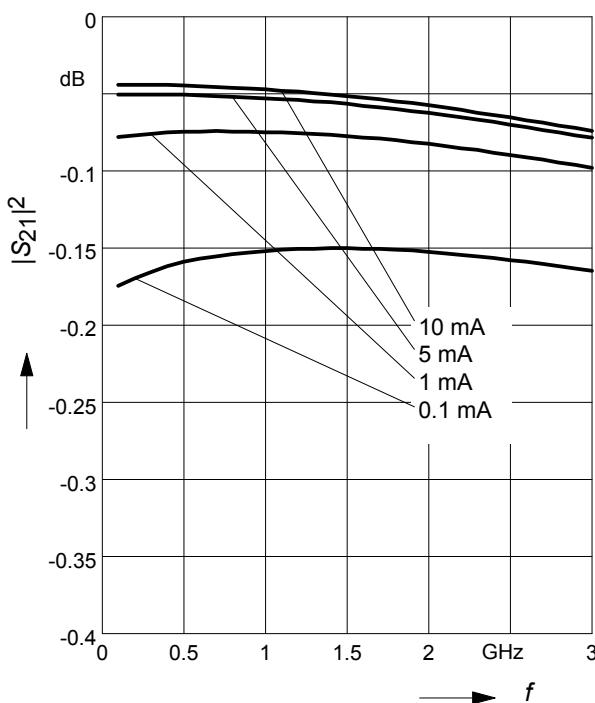
BAR65-03W

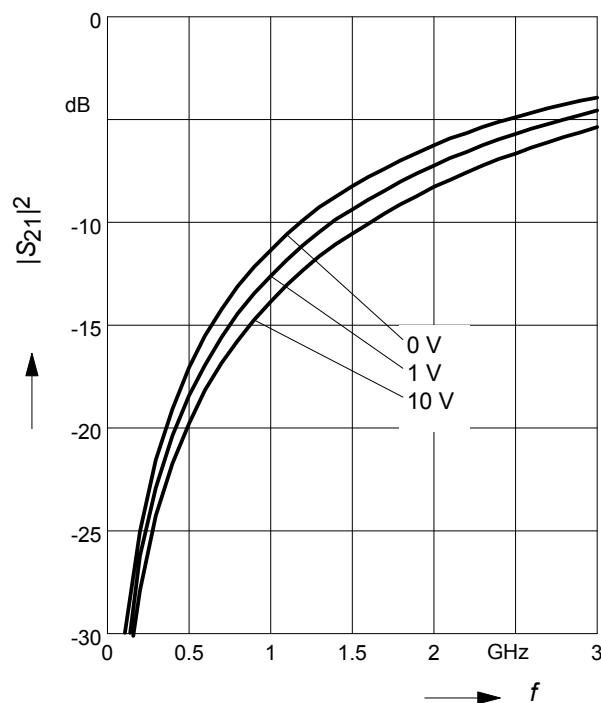

**Permissible Pulse Load**

$$I_{Fmax}/I_{FDC} = f(t_p)$$

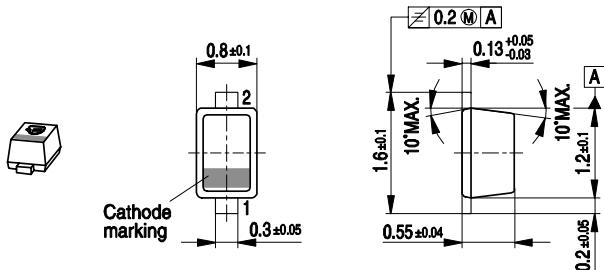
BAR65-03W


**Insertion loss  $I_L = -|S_{21}|^2 = f(f)$** 
 $I_F$  = Parameter

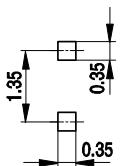
 BAR65-02L in series configuration,  $Z = 50\Omega$ 

**Isolation  $I_{SO} = -|S_{21}|^2 = f(f)$** 
 $V_R$  = Parameter

 BAR65-02L in series configuration  $Z = 50\Omega$ 


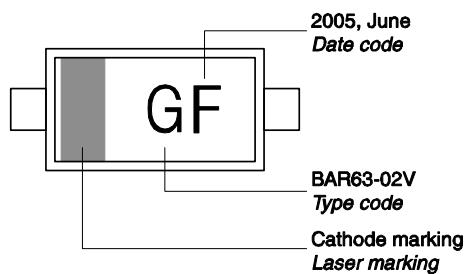
### Package Outline



### Foot Print

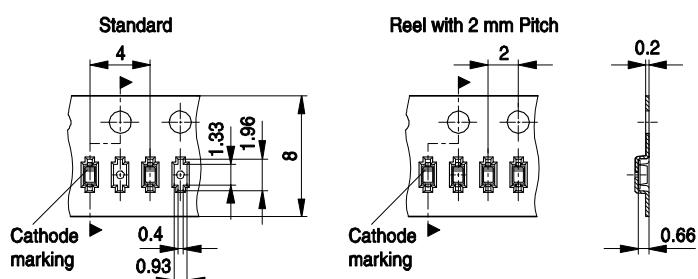


### Marking Layout (Example)



### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)  
 Reel ø330 mm = 10.000 Pieces/Reel

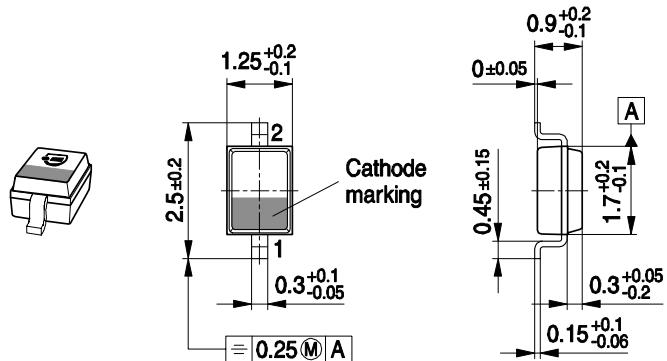


Date Code marking for discrete packages with  
one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

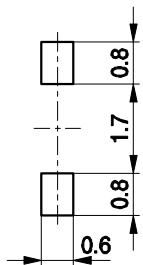
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

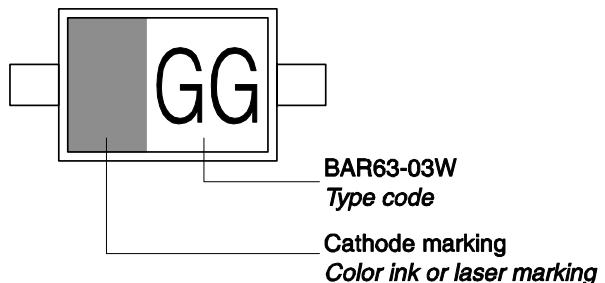
### Package Outline



### Foot Print

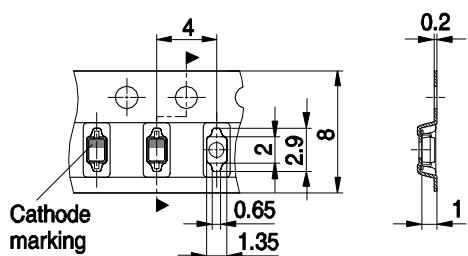


### Marking Layout (Example)

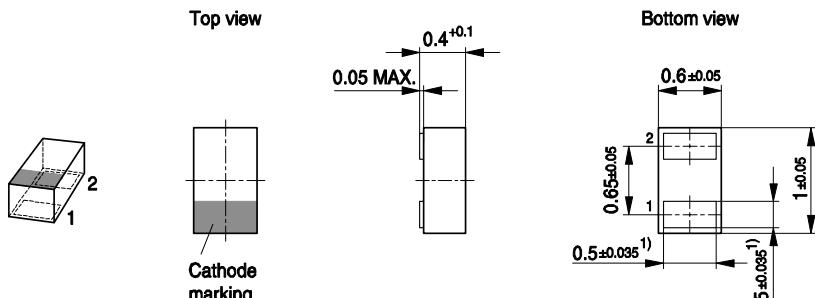


### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



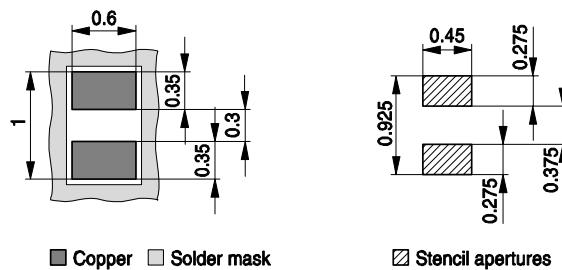
## Package Outline



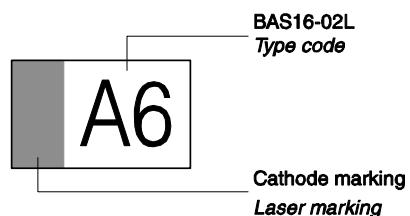
1) Dimension applies to plated terminal

## Foot Print

For board assembly information please refer to Infineon website "Packages"

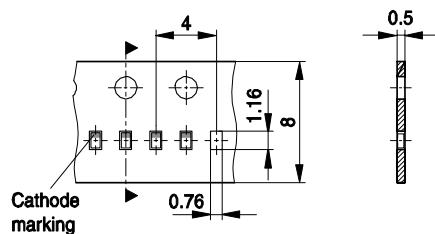


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel  
Reel ø330 mm = 50.000 Pieces/Reel (optional)



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